

isc Silicon NPN Power Transistor

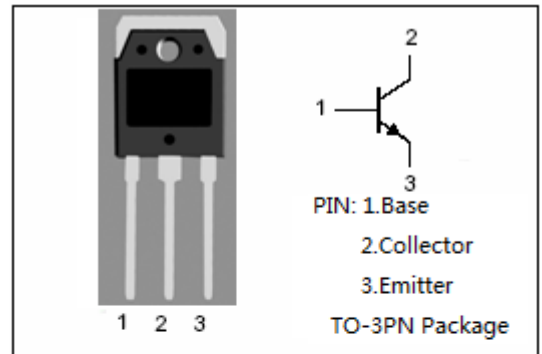
BU2527AW

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 800V(\text{Min})$
- High Switching Speed

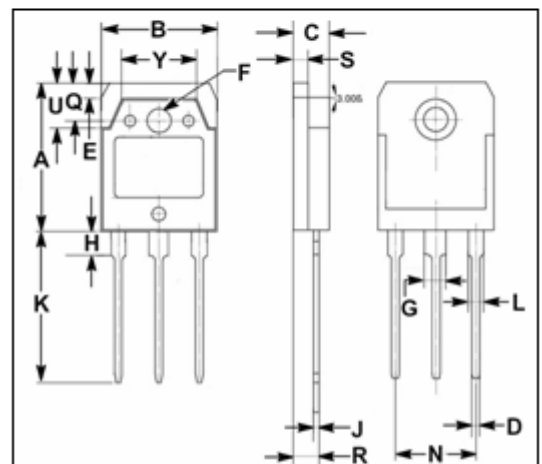
APPLICATIONS

- Designed for use in horizontal deflection circuits of high resolution monitors.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7.5	V
I_C	Collector Current-Continuous	12	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current-Continuous	8	A
I_{BM}	Base Current-Peak	12	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	125	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.0	$^\circ\text{C/W}$

isc Silicon NPN Power Transistor**BU2527AW****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 10mA; I _B = 0	800			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	7.5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 6A ; I _B = 1.2A			5.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 6A ; I _B = 1.2A			1.3	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 1500V ; I _E =0			0.25	mA
h _{FE-1}	DC Current Gain	I _C = 1A ; V _{CE} = 5V		10		
h _{FE-2}	DC Current Gain	I _C = 6A ; V _{CE} = 5V	5		9	
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = 10V; f _{test} = 1MHz		145		pF